

32nd RD50 Workshop (Hamburg)

Wednesday 6 June 2018

Defect and Material Characterization - Auditorium (09:20 - 13:00)

time	[id] title	presenter
09:20	[5] Measurements of NitroStrip detectors irradiated with 23MeV protons	BASELGA BACARDIT, Marta
09:40	[18] Forward and reverse current of highly irradiated silicon pad diodes	SCHARF, Christian
10:00	[24] FORMATION AND ELIMINATION OF RADIATION DEFECTS RESPONSIBLE FOR CHARGE CARRIER REMOVAL IN BORON DOPED SILICON	MAKARENKO, Leonid
10:20	[28] Characterization of acceptor removal in silicon pad diodes irradiated by protons and neutrons	DIAS DE ALMEIDA, Pedro
10:40	Coffee Break	
11:10	[37] A parametrization of initial acceptor removal	CARTIGLIA, Nicolo
11:30	[3] Application of p-i-n photodiodes to charged particle fluence measurements beyond 10^{15} 1-MeV-neutron-equivalent/cm ²	GRUMMER, Aidan
11:50	[13] First measurements with silicon detectors irradiated above $3e17$ n/cm ²	MANDIC, Igor
12:10	[39] Proposal for RD50 common project Mobility of carriers in irradiated Silicon	Prof. VAITKUS, Juozas VAITKUS, Juozas
12:30	[35] Discussion	PINTILIE, Ioana